| | Application No. | Applicant(s) |
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| | 0/802,907 | HSIUNG ET AL. |
| Notice of Allowability | xaminer | Art Unit |
| | Khanh B. Duong | 2822 |
| The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (O herewith (or previously mailed), a Notice of Allowance (PTOL-85) or NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGI of the Office or upon petition by the applicant. See 37 CFR 1.313 and | R REMAINS) CLOSED in this ap other appropriate communication HTS. This application is subject t | pplication. If not included n will be mailed in due course. THIS |
| 1. X This communication is responsive to the filing of the application | on March 17, 2004. | |
| 2. ☑ The allowed claim(s) is/are <u>1-8</u> . | | |
| Acknowledgment is made of a claim for foreign priority under a) All b) Some* c) None of the: Certified copies of the priority documents have been copies of the priority documents have been copies of the certified copies of the priority documents have been copies of the certified copies of the priority documents have been copies of the certified copies of the priority documents have been copies of the certified copies of the priority documents have been copies of the certified copies of the priority documents have been copies of the certified copies of the certified copies of the certified copies of the priority documents have been copies of the certified copies of the priority documents have been copies. | een received. een received in Application No | |
| Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMENTHIS THREE-MONTH PERIOD IS NOT EXTENDABLE. | | complying with the requirements |
| A SUBSTITUTE OATH OR DECLARATION must be submitted INFORMAL PATENT APPLICATION (PTO-152) which gives | | |
| 5. CORRECTED DRAWINGS (as "replacement sheets") must be | e submitted. | |
| (a) ☐ including changes required by the Notice of Draftsperson | s's Patent Drawing Review (PTO | -948) attached |
| 1) hereto or 2) to Paper No./Mail Date | | |
| (b) ☐ including changes required by the attached Examiner's A Paper No./Mail Date | mendment / Comment or in the (| Office action of |
| Identifying indicia such as the application number (see 37 CFR 1.84 each sheet. Replacement sheet(s) should be labeled as such in the | | |
| DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FO | | |
| | | |
| Attachment(s) | 5 Matica of Information | Datant Application (DTO 450) |
| 1. Notice of References Cited (PTO-892) | | Patent Application (PTO-152) |
| Notice of Draftperson's Patent Drawing Review (PTO-948) ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/08). | Interview Summary Paper No./Mail Da T. ☐ Examiner's Amend | te |
| Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit | _ | ent of Reasons for Allowance |
| of Biological Material | _ | on or readons for railonation |
| | 9. Other | ACCO FLOORING |

DETAILED ACTION

This Office Action is in response to the filing of the application on March 17, 2004.

Accordingly, claims 1-8 are pending.

Priority

Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Allowable Subject Matter

Claims 1-8 are allowed.

The following is an examiner's statement of reasons for allowance: none of the prior art of record, taken alone or in combination, fairly discloses all the limitations as claimed.

Re claim 1, none of the prior art of record discloses a method for fabricating a titanium nitride (TiN) sensing membrane on an extended gate field effect transistor (EGFET), comprising the steps of: depositing a layer of aluminum on a gate terminal of the EGFET using thermal evaporation, wherein the layer of aluminum extends from the gate terminal to a sensitive window of the EGFET; and forming the TiN sensing membrane on an exposed part of the layer of aluminum in the sensitive window as an ion sensitive sensor (pH sensor) using a radio frequency (RF) sputtering process during which TiN is used as a sputtering target and a mixture of argon and nitrogen in the ratio of 9:1 is used as a reactant.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

The following U.S. patents discloses relevant teachings regarding ions sensing devices: Lauks '380, Brown '566, Hsiung '075, Hsiung '081 and Chou '208. However, none of the cited patents fairly shows or suggests all the limitations as claimed.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khanh B. Duong whose telephone number is (571) 272-1836. The examiner can normally be reached on 10:00-6:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

KBD

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